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Microwave dielectric properties of Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ ceramics

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Abstract

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The microwave dielectric properties of ceramics based on Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ is investigated as a function of x. The densification as well as dielectric properties deteriorate with increase in the substitution levels of $(Ti_{1/3}W_{1/3})^{3.33+}$ at $(Ta_{2/3})^{3.33+}$ site in Ba(Mg_{1/3}Ta_{2/3})O₃. The τ_f is approaching zero between x = 0.1 and 0.15 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ where quality factor is reasonably good ($Q_u \times f = 80,000-90,000$ GHz). The Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ with x = 1.0 has $\varepsilon_r = 15.4$, $\tau_f = -25.1$ ppm/°C, $Q_u \times f = 35,400$ GHz.

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²⁰ Keywords: A. Ceramics; A. Oxides; C. X-ray diffraction; D. Crystal structure; D. Dielectric properties

1. Introduction

The complex perovskites Ba(Mg_{1/3}Ta_{2/3})O₃ [BMT] shows very interesting dielectric properties in the microwave 24 frequency region [1]. The crystal chemistry of A-site and B-site substitution in Ba- and Pb-based 1:2 ordered complex 25 perovskites are reported [2] to have tremendous influence on its physical and dielectric properties. The cation ordering 26 kinetics in Ba- and Pb-based ceramics are markedly different as the latter disorders even at very low-temperatures [3]. 27 The partial substitution of Ba with Sr in 1:2 ordered complex perovskites niobates have been investigated by a number 28 of investigators for possible applications in microwave communication devices [4]. There have been many attempts 29 [5,6] to predict the microwave dielectric properties by studying the solid solution phases in $Ba_{1-x}Sr_x(Mg_{1/3}Ta_{2/3})O_3$ 30 system, which provided valuable information about the structure-property relation of low-loss complex perovskites. 31 The barium in complex perovskites can be easily substituted with strontium ion as they are isovalent and have 32 comparable ionic radii (1.61 and 1.44 Å, respectively), which are the two important requirements for solid solution 33 formation. The complete replacement of Ba with Ca in the A-site of BMT was undertaken by Kagata and Kato [7] who 34 found a high quality factor of $Q_u \times f = 78,000$ GHz for Ca(Mg_{1/3}Ta_{2/3})O₃ ceramics. The substitution of a trivalent ion 35 (La) in A-site of BMT results in the coexistence of both 1:1 and 1:2 ordered domains [8,9]. The substitution at the B-36 site in Ba-based complex perovskites with tetravalent ion has been one of the most interesting part of the research on 37 complex perovskites as this imparts significant effects on the structural order of these materials [10]. 38

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The microwave dielectric properties of $Ba(Mg_{1/3}Ta_{2/3})O_3 - A(Mg_{1/2}W_{1/2})O_3$ [A = Ba, Sr and Ca] have been 39 investigated by Furuya and Ochi [11] who found that the presence of $Ba(Mg_{1/2}W_{1/2})O_3$ reduces the temperature 40 coefficient of resonant frequency for BMT. The duo could develop a zero $\tau_{\rm f}$ composition for 0.95Ba(Mg_{1/3}Ta_{2/3})O₃-41 0.05Ba(Mg_{1/2}W_{1/2})O₃ where the $Q_{\rm u} \times f$ value is reaching as high as 40,000 GHz. A significant attempt in this 42 direction was done by Takahashi et al. [12] who while investigating the microwave dielectric properties of 43 $(1 - x)Ba(Mg_{1/2}W_{1/2})O_3 - xBaTiO_3$ ceramics, found that for x = 2/3, the ceramics form a single phase (i.e. $Ba(Mg_{1/2})O_3 - xBaTiO_3 - xBATI$ 44 $_{3}Ti_{1/3}W_{1/3}O_{3}$) with low-dielectric constant and high quality factor. The above said composition is corresponding to 45 x = 1 in the Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ which in principle, is nothing, but a solid solution between Ta_{2/3} and W_{1/3} 46 $_{3}Ti_{1/3}$ in BMT. Even though, barium magnesium tantalate and barium zinc tantalate have attractive low-loss properties 47 and are extensively being used in microwave devices, the extremely high cost of the contributing raw material 48 tantalum pentoxide make them less attractive from an economic perspective. Hence, the searches for alternate low-loss 49 materials which are free of tantalum are being sought for active devices in telecommunication industry. So far no 50 useful work has been done on the aspect of simultaneous substitutional characteristics of W and Ti on the Ta site in 51 BMT which has been undertaken in this study. The present paper describes the variation of bulk density and microwave 52 dielectric properties of Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ system as a function of x. 53

2. Experimental

55 56 (0.8, 0.9 and 1.0) ceramics were prepared by the conventional mixed oxide route. High purity (>99.9%) powders of 57 BaCO₃, TiO₂, WO₃, (MgCO₃)4Mg(OH)₂·5H₂O (Aldrich Chemicals) and Ta₂O₅ (Nuclear Fuel Complex, 58 Hyderabad) were used as the starting materials. They were weighed according to the stoichiometric compositions 59 based on Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ [x = 0.0-1.0] and were ball milled in a plastic bottle using zirconia balls in deionized water for 24 h. The slurry was dried in an oven at 100 °C and calcined in platinum crucible at 1200 °C 60 for 10 h with intermediate grinding. The calcined powder was then ground for 2 h and 4 wt.% aqueous solution of 61 62 PVA was added to it as a binder. The powder was uniaxially pressed into cylindrical compacts of 14 mm diameter 63 and 6-8 mm thickness under a pressure of 150 MPa in tungsten carbide die. These compacts were fired at a rate of 5 °C/min up to 600 °C and soaked at 600 °C for 1 h to expel the binder before they were sintered in the temperature 64 range 1500-1600 °C for 4 h in air at a heating rate of 10 °C/h. The sintered samples were then cooled to 800 °C at a 65 slow rate of 60 °C/h and subsequently annealed at 1350 °C for 20 h. The polished ceramic pellets with an aspect 66 67 ratio (diameter to height) of 1.8-2.2 which is ideal for maximum separation of the modes, were used for microwave measurements. The bulk density of the sintered samples was measured using Archimedes method. The powdered 68 samples were used for analysing the X-ray diffraction patterns using Cu K α radiation (Philips X-ray 69



Fig. 1. Variation of bulk density of solid solution phases in $Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_3$ as a function of x.

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Diffractometer). The sintered samples were thermally etched for 30 min at a temperature of about 25 °C below the
sintering temperature and the surface morphology was studied using a scanning electron microscope (*JEOL-JSM* 5600 LV, Tokyo, Japan).

The dielectric properties of the materials were measured in the microwave frequency range using a network 73 74 analyser HP 8510 C (Hewlett-Packard, Palo Alto, CA). The dielectric constant ε_r was measured by the post resonator method of Hakki and Coleman [13] and the samples were end shorted with finely polished copper plates coated with 75 gold. The microwave is coupled though E-field probes as described by Courtney [14]. TE011 mode of resonance 76 whose Q is intimately related to the dielectric loss (tan δ), is used for the measurements. The unloaded quality factor 77 78 $Q_{\rm u}$ of the resonance was determined using a copper cavity whose interior was coated with silver and the ceramic 79 dielectric is placed on a low-loss quartz spacer which reduces effect of losses due to the surface resistivity of the cavity 80 [15]. For measuring the Q factor, the cavity method is ideal since the electric field is symmetrical with geometry of the cavity and the dielectric [16]. The coefficient of thermal variation of resonant frequency ($\tau_{\rm f}$) was measured by noting 81 the temperature variation of the resonant frequency of TE_{0 1 1} mode in the reflection configuration over a range of 82 temperature 20-80 °C when the sample was kept in the end shorted position. 83

3. Results and discussion

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The densification behavior of $Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_3$ phases is plotted in Fig. 1. Using the powder diffraction method, the theoretical density of BMT is calculated as 7.625 g/cm³ while that of $Ba(Mg_{1/3}W_{1/3}Ti_{1/3})O_3$



Fig. 2. The powder diffraction pattern of Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ [x = 0.1, 0.2, 0.3, 0.4, 0.5, 0.7, 0.9 and 1.0]: (\blacklozenge) represents TiO₂, (\Box) BaTiO₃.

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Table 1

The Miller indices of major powder diffraction profiles for x = 1.0 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ using a hexagonal superstructure of dimensions a = 5.79(1) and c = 14.16(2) Å

Peak no.	2θ (°)	d-Spacing (Å)	hkl
1 Tun-200 Wen That	12.43	7.121	002
2	17.67	5.018	100
3	22.12	4.018	102
4	25.17	3.538	004
5	25.81	3.453	103
6	27.44	3.250	011
7	28.12	3.173	113
8	30.67	2.915	110
9	31.10	2.876	220
10	37.11	2.423	. 113
11	38.23	2.354	202
12	40.11	2.248	114
13	41.07	2.197	203
14	43.20	2.094	121
15	44.12	2.053	204
16	47.76	1.906	205
18	49.83	1.829	212
19	53.71	1.706	213
20	54.62	1.680	300
21	55.90	1.645	301
22	58.43	1.579	215

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[17] is 6.412 g/cm³. As expected, the bulk density of compositions in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ decreases with x.

Fig. 2 represents the powder diffraction pattern of Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ [x = 0.1, 0.2, 0.3, 0.4, 0.5, 0.7, 0.9 and 1.0]. It is worthwhile to note that the low-loss ceramic system involving BaO-xMgO-yWO₃-zTiO₂ [x + y + z = 1] has already been investigated by Takahashi et al. [18]. They suggested a 1:1:1 cation ordering between Mg-W-Ti along (1 0 0) direction for x = 0.32, y = 0.32 and z = 0.68 in BaO-xMgO-yWO₃-zTiO₂. They attempted to index the XRD reflections based on a hexagonal unit cell ($a \sim 11.3$ Å = $2 \times \sqrt{2} \times 4$ Å; $c \sim 13.9$ Å = $2 \times \sqrt{3} \times 4$ Å)



Fig. 3. SEM picture of Ba(Mg_{0.333}Ta_{0.633}Ti_{0.016}W_{0.016})O₃.

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Fig. 4. Variation of the dielectric constant of Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ as a function of x.

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94 assuming a lattice constant $a \sim 4$ Å for the pseudo cubic unit cell [19]. In the present investigation also, the indexing of 95 the XRD pattern is done assuming a hexagonal unit cell with cell parameters a = 5.79(1) and c = 14.16(2) Å. Using the above assumption, the Miller indices for major reflections (for $10 \le 26 \le 60$) of the Ti + W rich end composition is 96 given in Table 1. However, based only on powder diffraction analysis, it may be erroneous to arrive at a conclusion 97 about the formation of an ordered phase with the composition $Ba(Mg_{1/3}Ti_{1/3}W_{1/3})O_3$ which corresponds to x = 1.0 in 98 $Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_3$ system. A more accurate structural analysis using electron microscopic and 99 100 spectroscopic tools is required to establish the 1:1:1 cation ordering between Mg–W–Ti along $(1 \ 0 \ 0)$ direction in $Ba(Mg_{1/3}Ti_{1/3}W_{1/3})O_3$, which is beyond the purview of this investigation. Also it is evident from Fig. 2 that when the 101 concentration levels of Ti + W increases, presence of trace amount of unreacted TiO₂ (JCPDS File Card Number 21-102 1276) was detected in the powder diffraction pattern (see Fig. 2). It is evident from the powder diffraction patterns that 103 the formation of trace amount of BaTiO₃ (JCPDS File Card Number 24-129) also detected for $0.5 \le x \le 0.9$. 104 Fig. 3 represents the scanning electron micrographs recorded from a typical samples for x = 0.05, in Ba(Mg₁/ 105

 ${}_{3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3}O_{3}$. This ceramic corresponds to the highest quality factor among all the compositions studied in 106 the present report and its average grain size is less than 5 µm. Since, no additional phases were visible in the SEM, one 107 can assume that addition of smaller percentages of W + Ti could have resulted in efficient substitution at the Ta site. 108 109



Fig. 5. Variation of the unloaded quality factor of $Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_3$ as a function of x.

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Fig. 4 is a plot describing the variation of the dielectric constant of the specimens with respect to the compositional variation of W + Ti against Ta. The measured values of dielectric constants were corrected for porosity [20]. For small values of x, the dielectric constant slightly increases (from 24.8 for x = 0.0, to 25.21 for x = 0.05 in Ba(Mg_{1/3}Ta_{(2-2x)/} ${}^{3}W_{x/3}Ti_{x/3})O_{3}$). Thereafter, ε_{r} decreases monotonically for higher values of x, reaching, 15.4 for x = 1.0 in Ba(Mg_{1/1} ${}^{3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_{3}$. This dielectric constant for the end composition, is in good agreement with a previous report by Takahashi et al. [18] who measured the ε_{r} of Ba(Mg_{1/3}Ti_{1/3}W_{1/3})O₃ as ~14.

The temperature coefficient of resonant frequency ($\tau_{\rm f}$) of the compositions in studied in the present investigation is 134 plotted in Fig. 4. The τ_f of stoichiometric Ba(Mg_{1/3}Ta_{2/3})O₃ is 8 ppm/°C which increases to 13.3 for x = 0.05 in 135 Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. It is evident from the Fig. 4 that the values of $\tau_{\rm f}$ for x = 0.1 and 0.15 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. 136 ${}_{3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3}O_{3}$ are 3.6 and -4.2 ppm/°C, respectively. This means that the temperature coefficient of resonant 137 frequency is approaching zero between x = 0.1 and 0.15 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. In general it is observed 138 that the $\tau_{\rm f}$ values of the compositions becomes more and more negative with increasing concentration of Ti + W 139 against Ta in Ba(Mg_{1/3}Ta_{2/3})O₃. The $\tau_{\rm f}$ for x = 1.0 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃, is -25.1 ppm/°C. This value is 140 move than thrice the $\tau_{\rm f}$ of Ba(Mg_{1/3}W_{1/3}Ti_{1/3})O₃ in a previous report [18] by Takahashi et al. (-7.6 ppm/°C), which is 141 expected to be due to the presence of BaTiO₃ in the Ti + W rich compositions. 142

The unloaded quality factor of compositions in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ is plotted in Fig. 5. It is evident that the quality factor of the composition for x = 1.0 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃, is inferior to that of the other end member, Ba(Mg_{1/3}Ta_{2/3})O₃. The quality factor varies from $Q_u \times f = 100,500$ to 35,400 GHz as x varies from 0 to 1.0 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. The lower value of quality factor of the latter may be attributed to its relatively lowdensification. It is worthwhile to note that for zero τ_f compositions in the present system (0.1 < x < 0.15 in Ba(Mg_{1/1} $_{3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O_3$), the quality factor is reasonably high ($Q_u \times f = 80,000-90,000$ GHz).

4. Conclusions

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150 The Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃ [x = 0.01, 0.02, 0.03, 0.04, 0.05, 0.1, 0.15, 0.2, 0.25, 0.3, 0.4, 0.5, 0.6, 0.7, 0.8, 0.9151 and 1.0] ceramics were prepared by the conventional mixed oxide route and their microwave dielectric properties were studied. The dielectric constant decreases, while the temperature coefficient of resonant frequency decreases and 152 153 approaches negative values with increase of x in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. The $\tau_{\rm f}$ approaches zero between x = 0.1154 and 0.15 in Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃. The microwave dielectric properties of Ba(Mg_{1/3}W_{1/3}Ti_{1/3})O₃ are $\varepsilon_r = 15.4$, $\tau_{\rm f} = -25.1 \text{ ppm}^{\circ}\text{C}$, $Q_{\rm u} \times f = 35,400 \text{ GHz}$. The zero $\tau_{\rm f}$ compositions in the present investigation (0.1 < x < 0.15 in 155 156 Ba(Mg_{1/3}Ta_{(2-2x)/3}W_{x/3}Ti_{x/3})O₃) have reasonably high quality factor ($Q_u \times f = 80,000-90,000$ GHz) which could be 157 used for practical dielectric resonator applications.

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